

N-Channel Super Junction Power MOSFET

General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

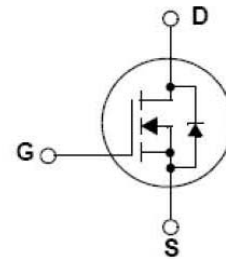
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

V_{DS}	650	V
$R_{DS(ON) MAX}$	80	mΩ
I_D	69	A



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
HMS47N65A	TO-3P	HMS47N65A

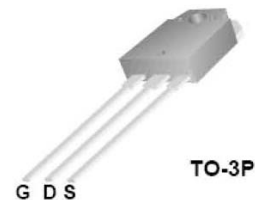


Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	HMS47N65A	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$)	V_{GS}	± 30	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	47	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	33	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	141	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	200	W
Derate above 25°C		1.6	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	690	mJ
Avalanche current (Note 1)	I_{AR}	7	A
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	1	mJ

Parameter	Symbol	HMS47N65A	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	HMS47N65A	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.62	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62.5	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current($T_C=25^\circ C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$		0.05	1	μA
Zero Gate Voltage Drain Current($T_C=125^\circ C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10.5A$			80	m Ω
Dynamic Characteristics						
Forward Transconductance	g_{FS}	$V_{DS} = 20V, I_D = 10.5A$		17.5		S
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		1950		PF
Output Capacitance	C_{oss}			150		PF
Reverse Transfer Capacitance	C_{rss}			5		PF
Total Gate Charge	Q_g		$V_{DS}=480V, I_D=47A,$ $V_{GS}=10V$		45	70
Gate-Source Charge	Q_{gs}			9		nC
Gate-Drain Charge	Q_{gd}			18		nC
Intrinsic gate resistance	R_G	$f = 1 MHz$ open drain		1		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=11A,$ $R_G=4\Omega, V_{GS}=10V$		11		nS
Turn-on Rise Time	t_r			6		nS
Turn-Off Delay Time	$t_{d(off)}$			61	100	nS
Turn-Off Fall Time	t_f			4.5	12	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^\circ C$			47	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				141	A
Forward on voltage	V_{SD}	$T_J=25^\circ C, I_{SD}=47A, V_{GS}=0V$		0.9	1.3	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ C, I_F=47A, di/dt=100A/\mu s$		310		nS
Reverse Recovery Charge	Q_{rr}				5	μC
Peak Reverse Recovery Current	I_{rrm}				28	A

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

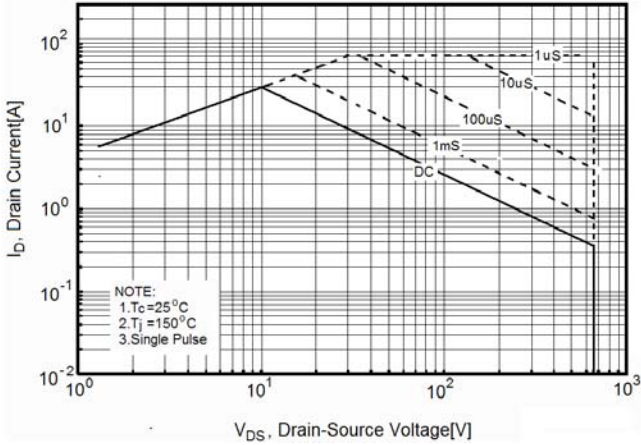


Figure3. Source-Drain Diode Forward Voltage

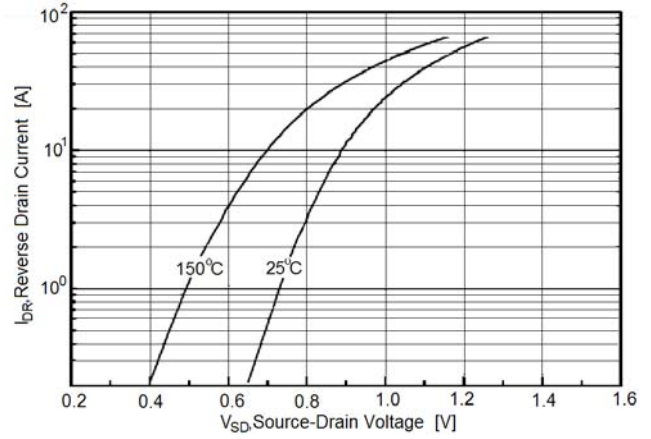


Figure4. Output characteristics

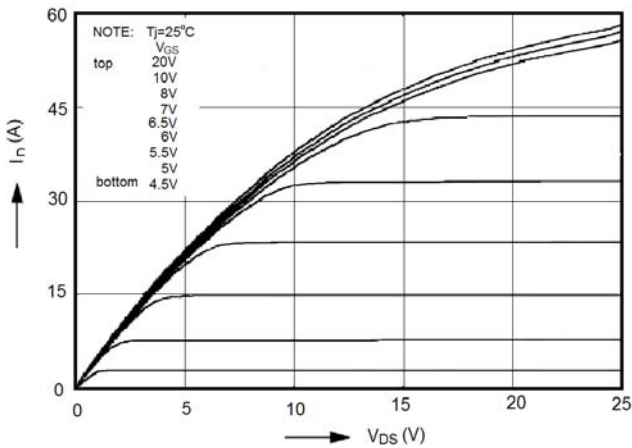


Figure5. Transfer characteristics

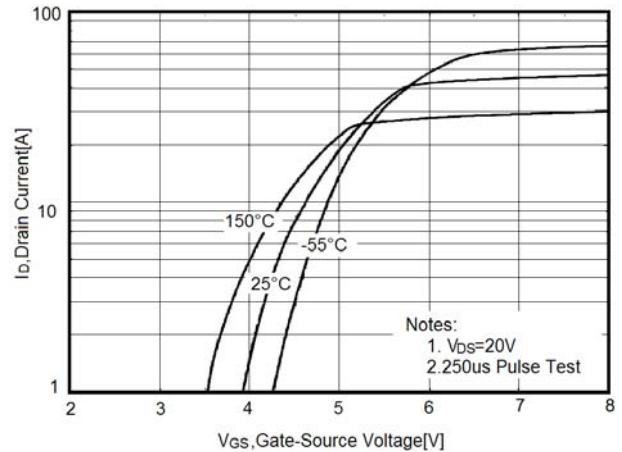


Figure6. Static drain-source on resistance

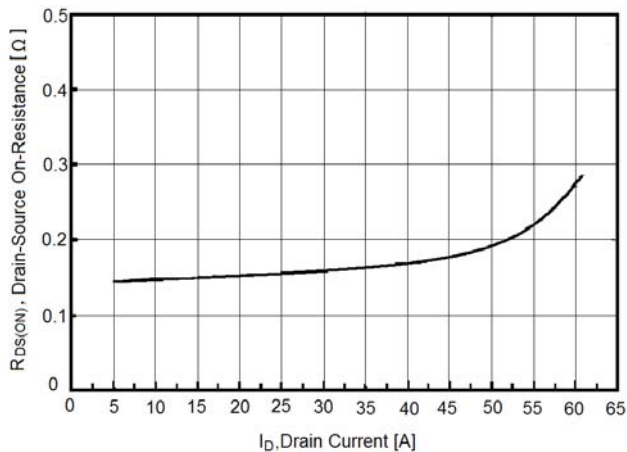


Figure7. $R_{DS(ON)}$ vs Junction Temperature

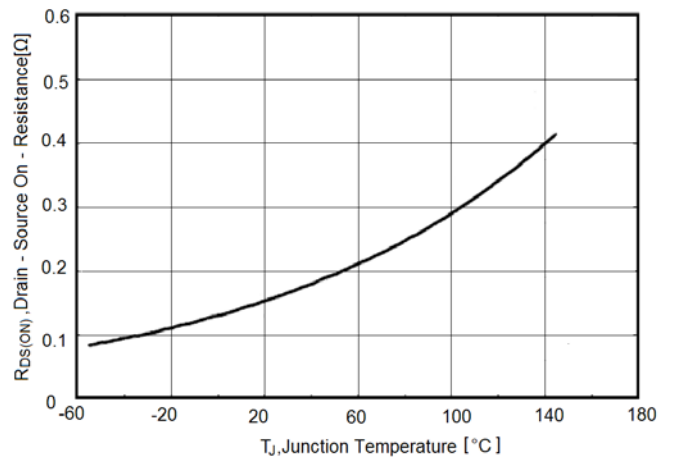


Figure8. V_{DS} vs Junction Temperature

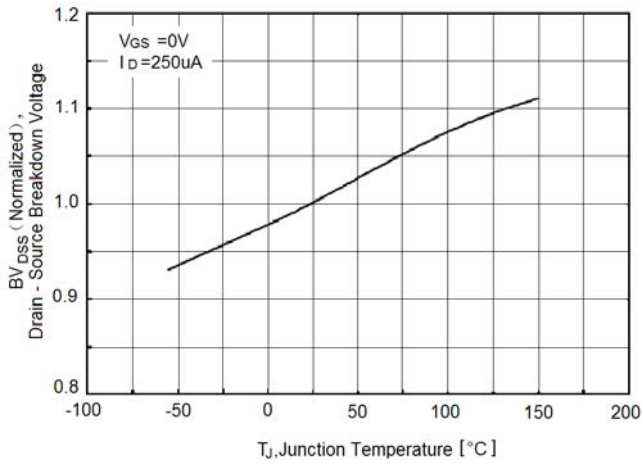


Figure9. Maximum I_D vs Junction Temperature

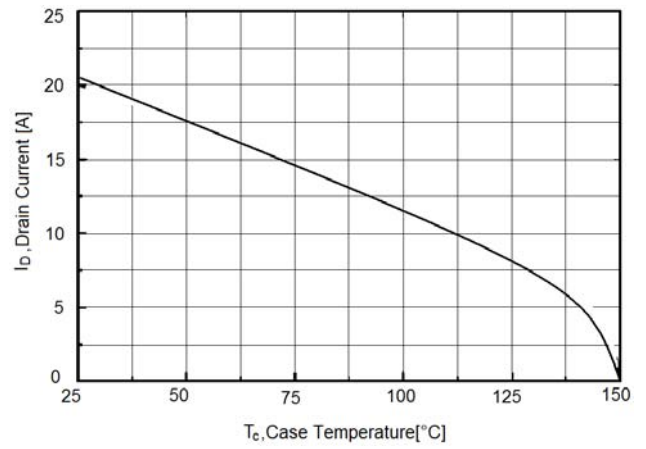


Figure10. Gate charge waveforms

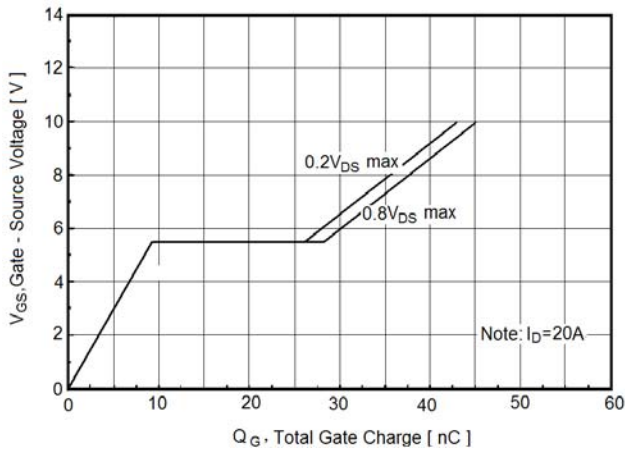


Figure11. Capacitance

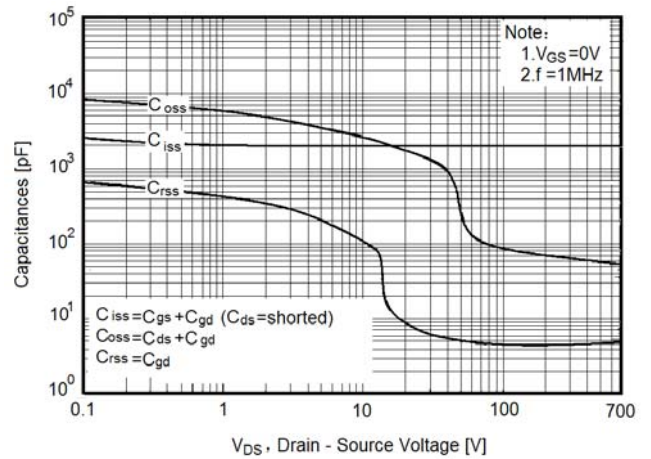
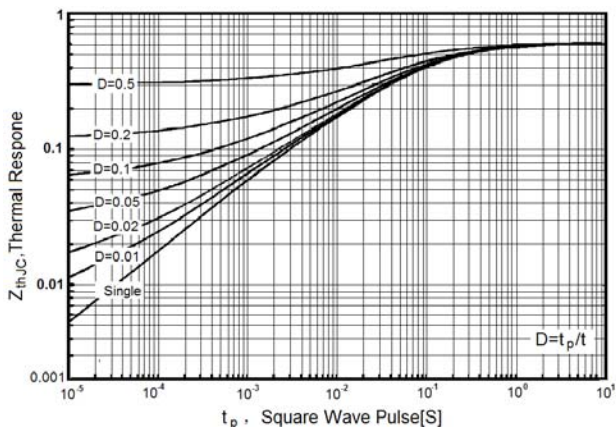
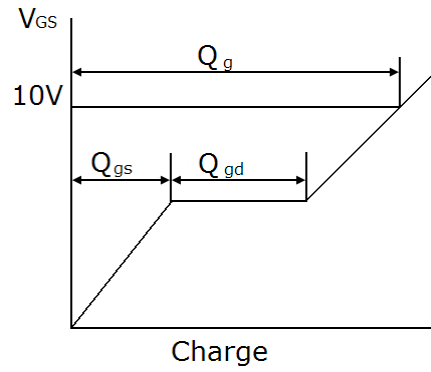
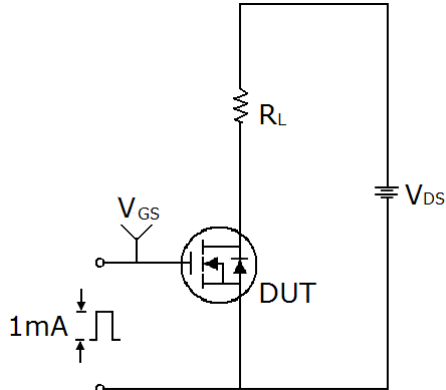


Figure12. Transient Thermal Impedance

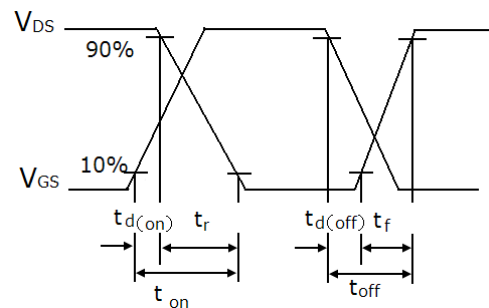
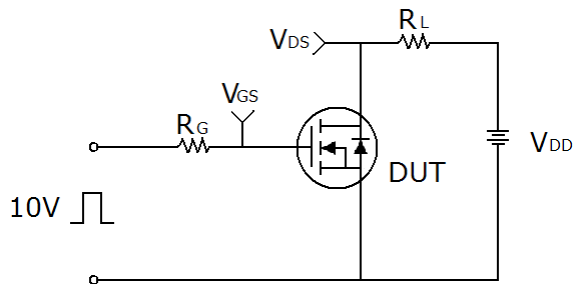


Test circuit

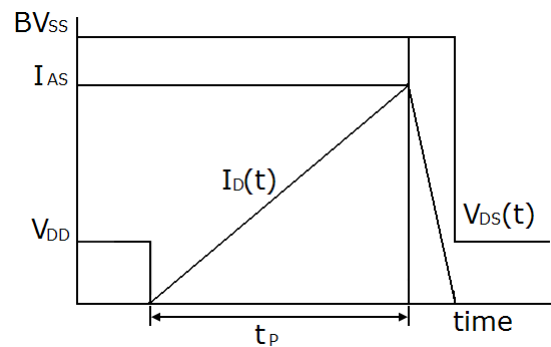
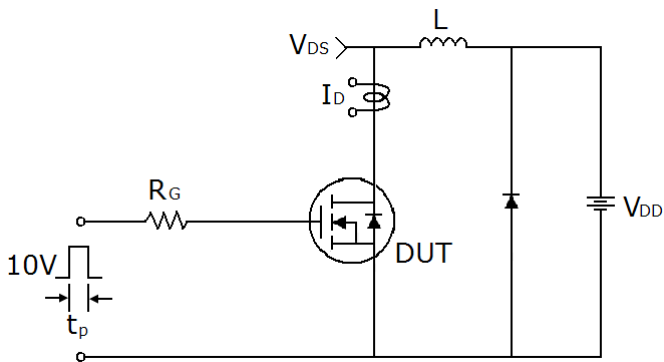
1) Gate charge test circuit & Waveform



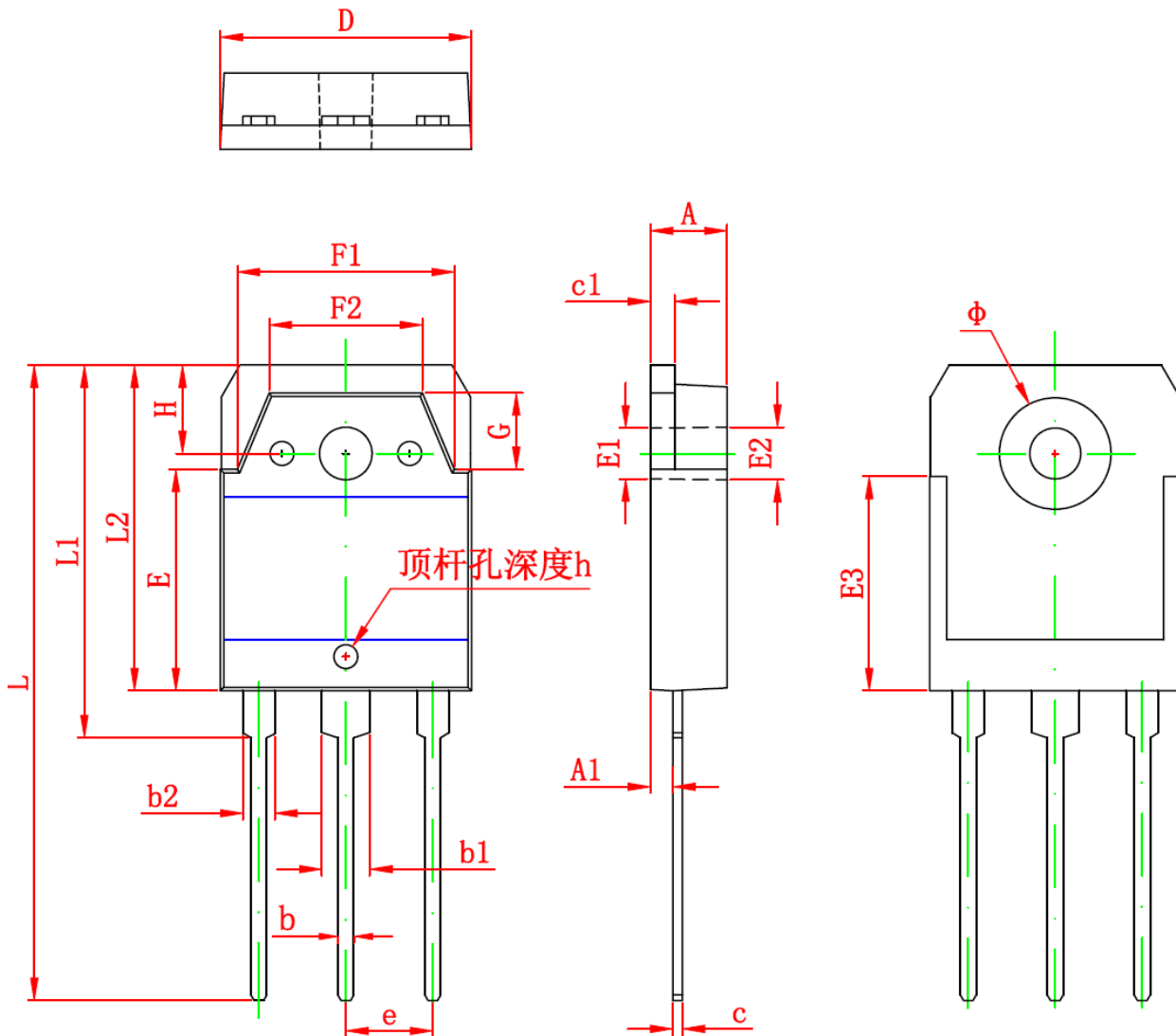
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



TO-3P PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.600	5.000	0.181	0.197
A1	1.200	1.600	0.047	0.063
b	0.800	1.200	0.031	0.047
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.450	1.650	0.057	0.065
D	15.450	15.850	0.606	0.622
E	13.700	14.100	0.539	0.555
E1	3.200 REF		0.126 REF	
E2	3.300 REF		0.130 REF	
E3	13.450 REF		0.530 REF	
F1	13.400	13.800	0.528	0.543
F2	9.400	9.800	0.370	0.386
L	39.900	40.300	1.571	1.587
L1	23.200	23.600	0.913	0.929
L2	20.300	20.600	0.799	0.811
Φ	6.900	7.100	0.272	0.280
G	5.150	5.550	0.203	0.219
e	5.450 TYP		0.215 TYP	
H	5.000 REF		0.197 REF	
h	0.000	0.300	0.000	0.012

Attention:

- Any and all H&M SEMI products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your H&M SEMI representative nearest you before using any H&M SEMI products described or contained herein in such applications.
- H&M SEMI assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all H&M SEMI products described or contained herein.
- Specifications of any and all H&M SEMI products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- H&M Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all H&M SEMI products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of H&M Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. H&M SEMI believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the H&M SEMI product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.